Notice of Allowability	Applicati n No.	Applicant(s)	
	09/857,453 Examiner	KING ET AL.	
	Victor A Mandala Jr.	2826	
	Victor A Maridala Jr.	2020	
The MAILING DATE of this communication at All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOLNOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.	SIS (OR REMAINS) CLOSED in table 85) or other appropriate communing RIGHTS. This application is su	his application. If not incluication will be mailed in du	ded e course. THIS
1. This communication is responsive to <u>Amendment C file</u>	ed 10/16/03.		
2. The allowed claim(s) is/are <u>21-23 and 26-32</u> .		10 1/19	
3. The drawings filed on <u>04 June 2001</u> are accepted by the		WE WILL	Proposition of
 4.	y under 35 U.S.C. § 119(a)-(d) or	(f). 3550	
All by Some cy Notice of the. 1. ☐ Certified copies of the priority documents h	nave heen received		
2. ☐ Certified copies of the priority documents h		No.	
3. \(\subseteq Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)		ar and riduorial olago applic	
* Certified copies not received:	,		
5. Acknowledgment is made of a claim for domestic priorit reference was included in the first sentence of the spec			ce a specific
(a) The translation of the foreign language provision	al application has been received.		
 Acknowledgment is made of a claim for domestic priorities in the first sentence of the specification or in an Application. 		121 since a specific refere	nce was included
Applicant has THREE MONTHS FROM THE "MAILING DATE below. Failure to timely comply will result in ABANDONMENT			
7. A SUBSTITUTE OATH OR DECLARATION must be su INFORMAL PATENT APPLICATION (PTO-152) which			NOTICE OF
8. CORRECTED DRAWINGS (as "replacement sheets")	must be submitted.		
(a) 🔲 including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached			
1) ☐ hereto or 2) ☐ to Paper No			
(b) including changes required by the proposed drawing correction filed, which has been approved by the Examiner.			
(c) including changes required by the attached Examir	ner's Amendment / Comment or in	n the Office action of Paper	No
Identifying indicia such as the application number (see 37 CF each sheet. Replacement sheet(s) should be labeled as such			ne back) of
9. DEPOSIT OF and/or INFORMATION about the deattached Examiner's comment regarding REQUIREMENT FO			Note the
Attachm nt(s)			
1⊠ Notice of References Cited (PTO-892)	5☐ Notice of Inform	mal Patent Application (PT	O-152)
2 Notice of Draftperson's Patent Drawing Review (PTO-948	-	mary (PTO-413), Paper No	
3 Information Disclosure Statements (PTO-1449 or PTO/SE Paper No	^{3/08),} 7⊠ Examiner's An	nendment/Comment	
4	t 8⊠ Examiner's Sta 9⊡ Other .	atement of Reasons for Allo	owance

- - -

U.S. Patent and Trademark Office

DETAILED ACTION

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

1. The examiner amends the specification by the addition of an abstract as written below:

Abstract

A semiconductor device including a gate oxide of multiple thicknesses for multiple transistors where the gate oxide thicknesses are altered through the growth process of implanted oxygen ions into selected regions of a substrate. The implanted oxygen ions accelerate the growth of the oxide which also allow superior quality and reliability of the oxide layer, where the quality is especially important, compared to inter-metal dielectric layers. A technique has been used to vary the thickness of an oxide layer grown on a silicon wafer during oxidation growth process by implanting nitrogen into selected regions of the substrate, which the nitrogen ions retard the growth of the silicon oxide resulting in a diminished oxide quality. Therefore it is desirable to fabricate a semiconductor device with multiple thicknesses of gate oxide by the implanted oxygen ion technique.

Application/Control Number: 09/857,453

Art Unit: 2826

Page 3

Allowable Subject Matter

The following is an examiner's statement of reasons for allowance:

2. The Applicant has argued the allowability of claims 21-23 and 26-32 in Amendment C

filed on 9/08/03. The Applicant discusses that the divisional, #09/449063, of this application has

gone to Appeal on very similar claims to claims 21-23 and 26-32 of this application, which the

rejections in Application #09/449063 where also very similar to the rejections at hand, and the

Board of Appeals has reversed the rejections in Application #09/449063. The examiner has

considered the Applicant's arguments and finds them to be persuasive.

3. Claims 21-23 & 26-32 are allowed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

Conclusion

Page 4

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Victor A Mandala Jr. whose telephone number is (703) 308-6560.

The examiner can normally be reached on Monday through Thursday from 8am till 6pm..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Nathan Flynn can be reached on (703) 308-6601. The fax phone number for the

organization where this application or proceeding is assigned is (703) 872-9318.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-0956.

VAMJ 1/22/04